

SESDFBPxxV Series
Single Line ESD Protection Diode

Revision:B

General Description

The SESDFBPxxV ESD protection diode is designed to replace multilayer varistors (MLVs) in portable applications such as cell phones, notebook computers, and PDA's. They feature large cross-sectional area junctions for conducting high transient currents, offer desirable electrical characteristics for board level protection, such as fast response time, lower operating voltage, lower clamping voltage and no device degradation when compared to MLVs.

Applications

- Cellular phones handsets and Accessories
- PDA's
- MP3 players
- Digital cameras
- Portable applications
- mobile telephone

Features

- 60W peak pulse power
- Small package for use in portable electronics
- Low leakage current
- These are Pb-Free Devices

Complies with the following standards

IEC61000-4-2

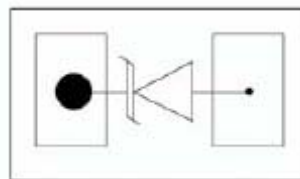
Level 4 15 kV (air discharge)

8 kV(contact discharge)

MIL STD 883E - Method 3015-7 Class 3

25 kV HBM (Human Body Model)

Functional diagram



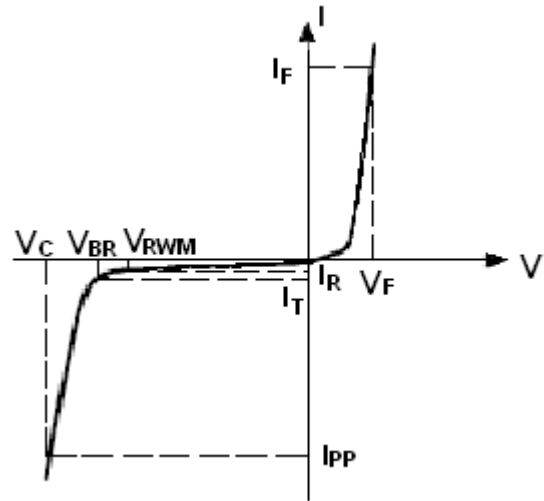
WBFBP-02C

Maximum Ratings

Symbol	Parameter	Value	Unit
V _{PP}	IEC 61000-4-2 (ESD) Contact	±15	kV
P _{PK}	Peak Pulse Power	60	W
I _{PP}	Peak Pulse Power	12	A
T _J , T _{STG}	Junction and Storage Temperature Range	-55 to 150	°C
T _L	Lead Solder Temperature – Maximum (10 Second Duration)	260	°C

Electrical Parameter

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
I_T	Test Current
V_{BR}	Breakdown Voltage @ I_T
I_F	Forward Current
V_F	Forward Voltage @ I_F



Electrical Characteristics ($T_A=25^{\circ}C$ unless otherwise noted, $V_F=1.25V$ Max. @ $I_F=10mA$ for all types)

Part Numbers	V_{BR}			I_T	V_{RWM}	I_R	C
	Min.	Typ.	Max.				Max. 1MHz, 0V Bias (note 1)
	V	V	V				pF
SESDFBP3V3	5.0	5.7	6.4	1	3.3	1	35
SESDFBP05V	6.0	6.8	7.2	1	5.0	1	30
SESDFBP07V	7.5	8.1	8.6	1	7.0	1	25
SESDFBP12V	13.5	14.2	15.0	1	12.0	1	15

1. Capacitance of one diode at $f=1MHz, V_{RW}=0V, T_A=25^{\circ}C$

Typical Characteristics

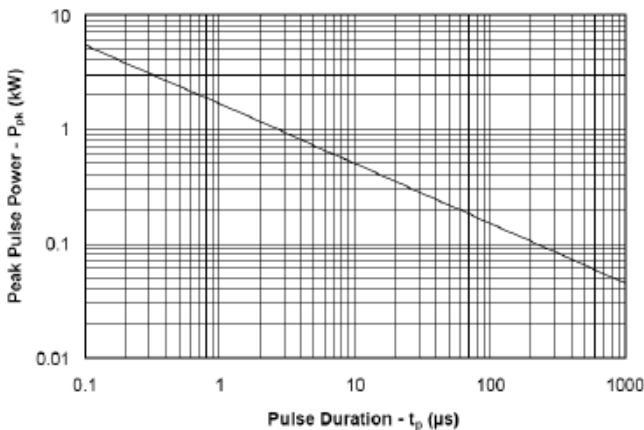


Figure 1. Non-Repetitive Peak Pulse Power versus Pulse Time

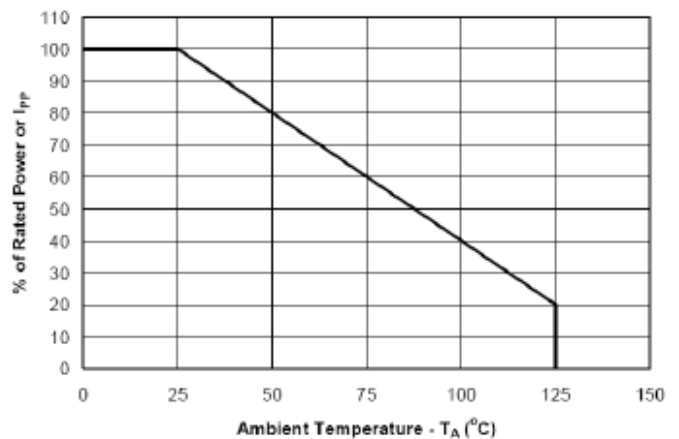


Fig 2. Power Derating Curve

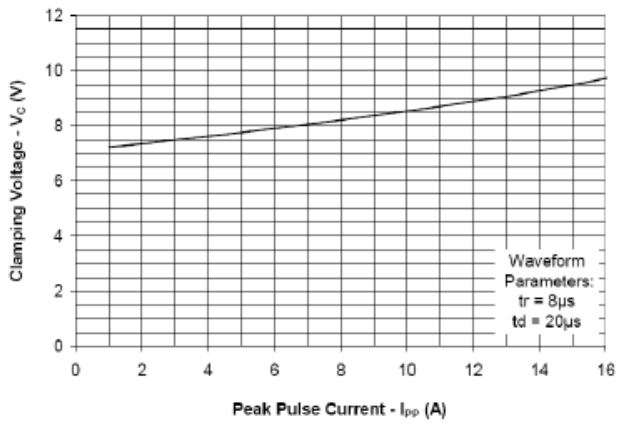


Figure 3. Clamping Voltage vs. Peak Pulse Current

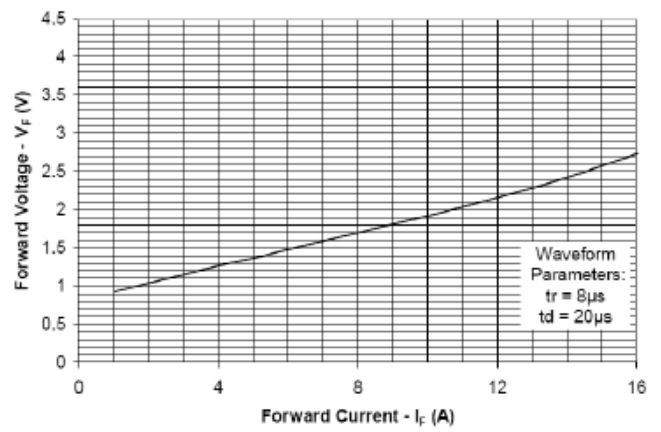


Figure 4. Forward Voltage vs. Forward Current

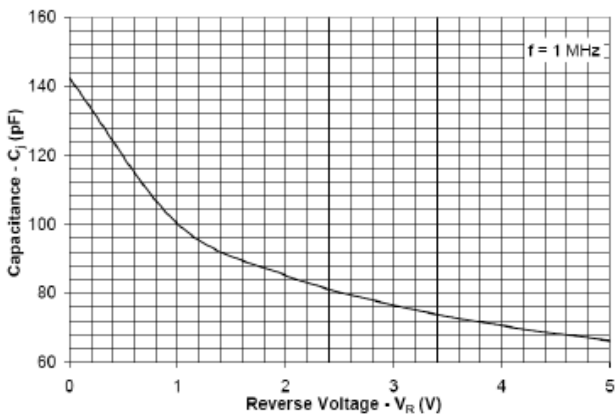


Figure 5. Junction Capacitance vs. Reverse Voltage

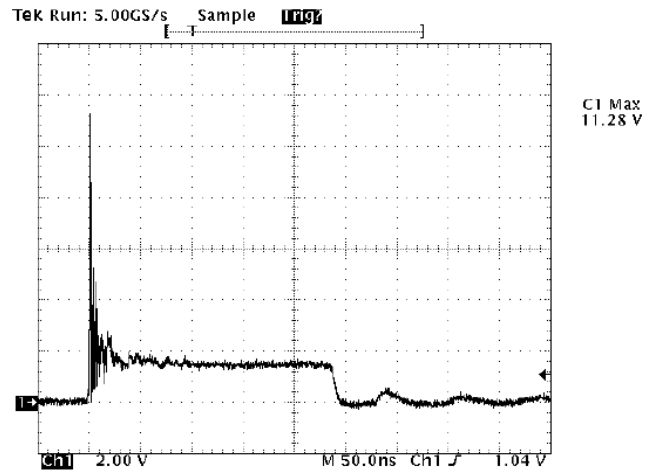
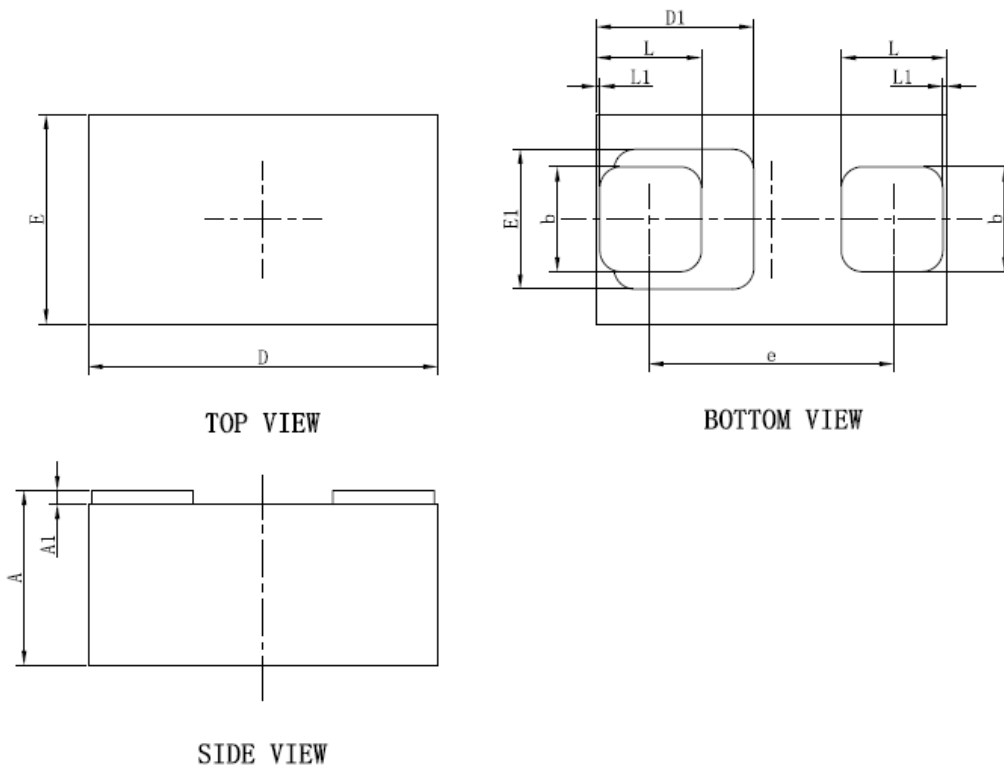


Fig 6. ESD Clamping (8kV Contact per IEC 61000-4-2)

WBFBP-02C Mechanical Data



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.450	0.550	0.018	0.022
A1	0.010	0.070	0.000	0.003
D	0.950	1.050	0.037	0.041
E	0.550	0.650	0.022	0.026
D1	0.450REF.		0.018REF.	
E1	0.400REF.		0.016REF.	
b	0.275	0.325	0.011	0.013
e	0.675	0.725	0.027	0.029
L	0.275	0.325	0.011	0.013
L1	0.010REF.		0.000REF.	

The SINO-IC logo is a registered trademark of ShangHai Sino-IC Microelectronics Co., Ltd.

© 2005 SINO-IC – Printed in China – All rights reserved.

SHANGHAI SINO-IC MICROELECTRONICS CO., LTD

Add: Building 3, Room 3401-03, No.200 Zhangheng Road, ZhangJiang Hi-Tech Park, Pudong, Shanghai 201203, China

Phone: +86-21-33932402 33932403 33932405 33933508 33933608

Fax: +86-21-33932401

Email: webmaster@sino-ic.com

Website: <http://www.sino-ic.com>